

P/N: YZPST-2SC4793
Silicon NPN Power Transistor
DESCRIPTION

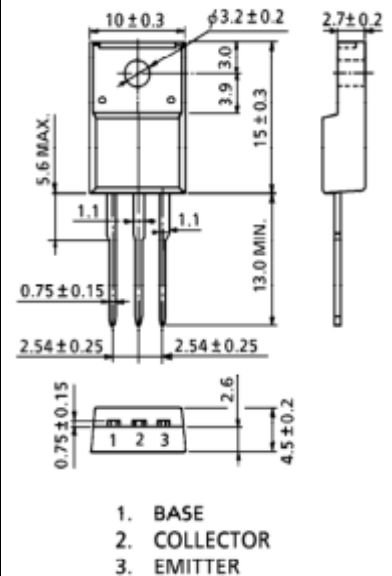
- Collector-Emitter Breakdown Voltage- $V_{(BR)CEO} = 230V$ (Min)
- High Current-Gain Bandwidth Product
- Complement to Type 2SA1837
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier applications

Maximum ratings(Ta=25°C unless otherwise noted)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	230	V	
Collector-emitter voltage	V_{CEO}	230	V	
Emitter-base voltage	V_{EBO}	5	V	
Collector current	I_C	1	A	
Base current	I_B	0.1	A	
Collector power dissipation	P_C	Ta = 25°C	2	W
		Tc = 25°C	20	
Junction temperature	T_j	150	°C	
Storage temperature range	T_{stg}	-55 to 150	°C	


Electrical Characteristics (Ta=25°C unless otherwise noted)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 230V, I_E = 0$	—	—	1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$	—	—	1	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	230	—	—	V
DC current gain	h_{FE}	$V_{CE} = 5V, I_C = 100mA$	100	—	320	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500mA, I_B = 50mA$	—	—	1.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 5V, I_C = 500mA$	—	—	1	V
Transition frequency	f_T	$V_{CE} = 10V, I_C = 100mA$	—	100	—	MHz
Collector output capacitance	C_{ob}	$V_{CB} = 10V, f = 1MHz$	—	20	—	pF

Typical Characteristics

